

Silicon NPN Power Transistors

2SC2987

DESCRIPTION

- With TO-3PN package
- Complement to type 2SA1227
- High power dissipation

APPLICATIONS

- For audio frequency power amplifier applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

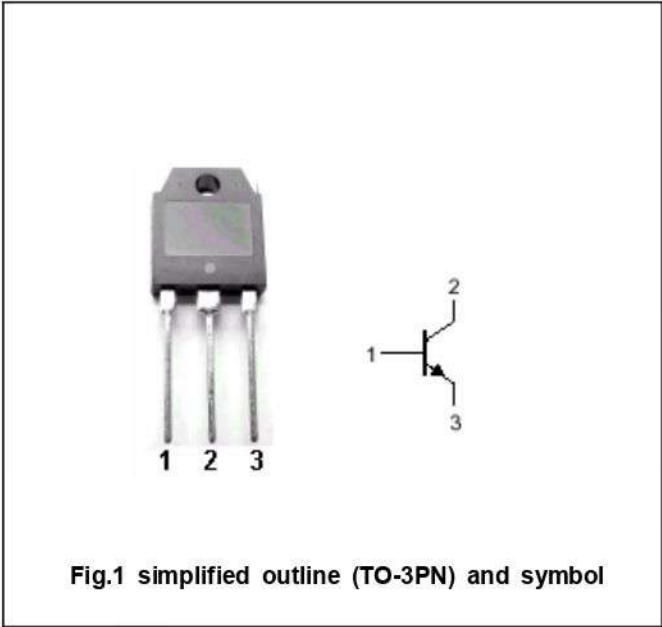


Fig.1 simplified outline (TO-3PN) and symbol

Absolute maximum ratings(Ta=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	140	V
V _{CEO}	Collector-emitter voltage	Open base	140	V
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current (DC)		12	A
I _{CM}	Collector current-peak		20	A
P _C	Collector power dissipation	T _C =25℃	120	W
T _j	Junction temperature		150	℃
T _{stg}	Storage temperature		-55~150	℃

Silicon NPN Power Transistors**2SC2987****CHARACTERISTICS****T_j=25°C** unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEsat}	Collector-emitter saturation voltage	I _C =5A ; I _B =0.5A		0.6	1.5	V
V _{BEsat}	Base-emitter saturation voltage	I _C =5A ; I _B =0.5A		1.4	2.0	V
I _{CBO}	Collector cut-off current	V _{CB} =140V; I _E =0			50	μA
I _{EBO}	Emitter cut-off current	V _{EB} =3V; I _C =0			50	μA
h _{FE-1}	DC current gain	I _C =2A ; V _{CE} =5V	60		320	
h _{FE-2}	DC current gain	I _C =5A ; V _{CE} =5V	40			
f _T	Transition frequency	I _C =1A ; V _{CE} =5V		50		MHz
C _{OB}	Collector output capacitance	I _E =0; f=1MHz; V _{CB} =10V		190		pF

◆ **h_{FE-1} Classifications**

R	Q	P
60-120	100-200	160-320

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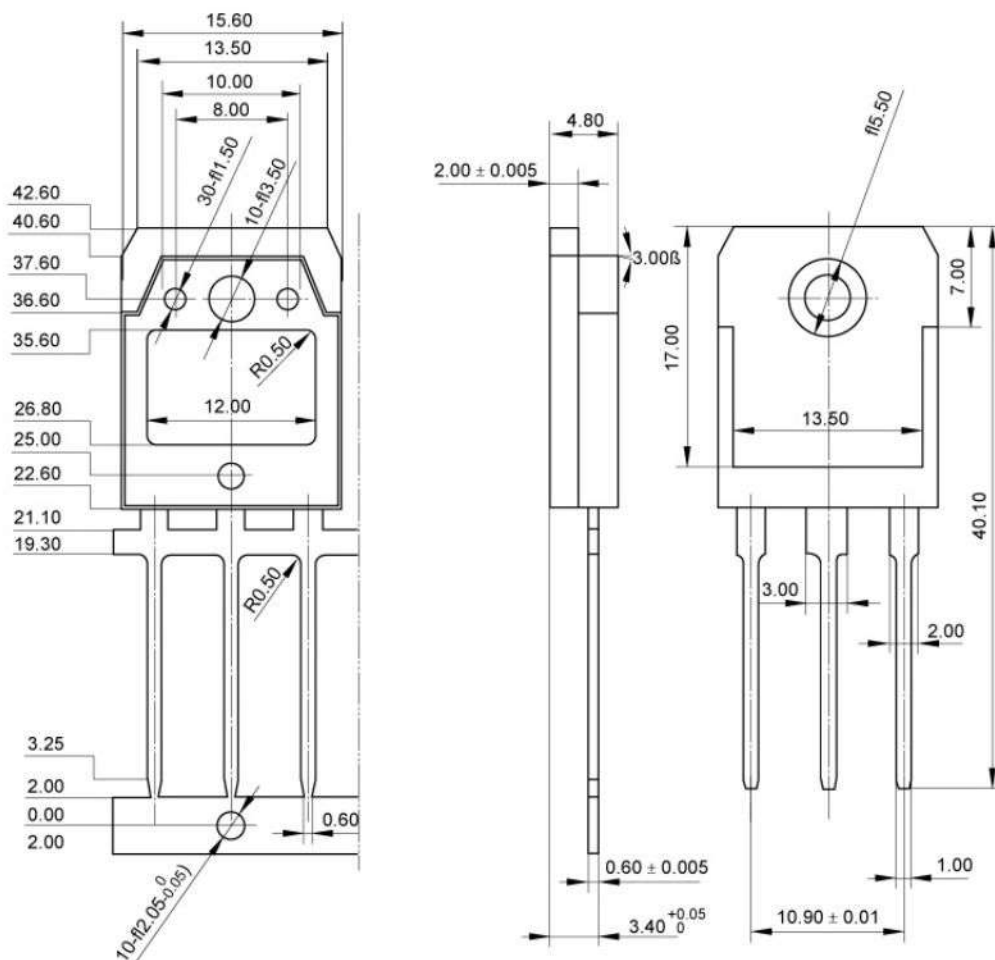


Fig.2 outline dimensions